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FXLA102 Low-Voltage Dual-Supply 2-Bit Voltage Translator with Configurable Voltage Supplies and Signal Levels, 3-State Outputs, and Auto Direction Sensing

Features

- Bi-Directional Interface betw een Tw o Levels: from 1.1 V to 3. 6V
- Fully Configurable: Inputs and Outputs Track V_{CC} Level
- Non-Preferential Pow er-Up; Either V_{CC} May Be Pow ered Up First
- Outputs Switch to 3-State if Either V_{CC} is at GND
- Pow er-Off Protection
- Bus-Hold on Data Inputs Eliminates the Need for Pull-Up Resistors; Do Not Use Pull-Up Resistors on A or B Ports
- Control Input (/OE) Referenced to V_{CCA} Voltage
- Packaged in MicroPak[™] 8 (1.6 mm x 1.6 mm)
- Direction Control Not Necessary
- 100 Mbps Throughput when Translating Between
 1.8 V and 2.5 V
- ESD Protection Exceeds:
 - 15 kV HBM ((B Port I/O to GND) per JESD22-A114 & Mil Std 883e 3015.7)
 - 8 kV HBM ((A Port I/O to GND) per JESD22-A114 & Mil Std 883e 3015.7)
 - 2 kV CDM (per ESD STM 5.3)

Description

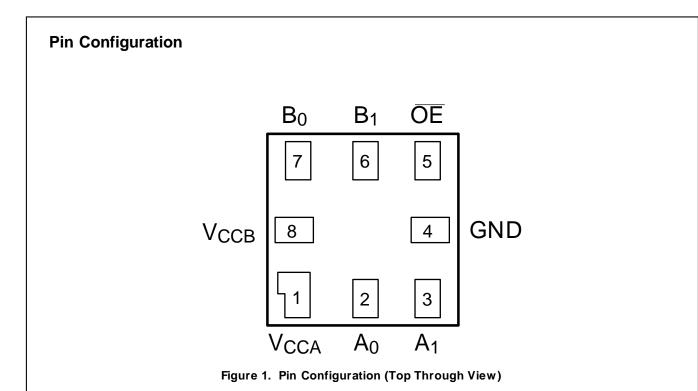
The FXLA102 is a configurable dual-voltage supply translator for both uni-directional and bi-directional voltage translation betw een two logic levels. The device allows translation betw een voltages as high as 3.6 V to as low as 1.1 V. The A port tracks the V_{CCA} level and the B port tracks the V_{CCB} level. This allows for bi-directional voltage translation over a variety of voltage levels: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V.

The device remains in three-state as long as either V_{CC} =0 V, allowing either V_{CC} to be powered up first. Internal power-down control circuits place the device in 3-state if either V_{CC} is removed.

The /OE input, when HIGH, disables both the A and B ports by placing them in a 3-state condition. The /OE input is supplied by $V_{\rm CCA}.$

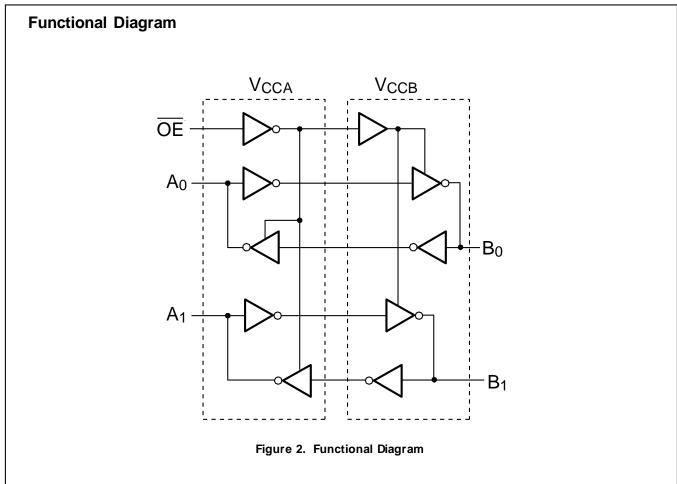
The FXLA102 supports bi-directional translation without the need for a direction control pin. The two ports of the device have auto-direction sense capability. Either port may sense an input signal and transfer it as an output signal to the other port.

Part Number	Top Mark	Operating Temperature Range	Package	Packing Method
FXLA102L8X	XF	-40 to 85°C	8-Lead MicroPak [™] 1.6 mm x 1.6 mm Package	5 K Units Tape and Reel



Pin Definitions

Pin #	Name	Description
1	V _{CCA}	A-Side Pow er Supply
2	A ₀	A Side Input or 3-State Output
3	A ₁	A Side Input or 3-State Output
4	GND	Ground
5	/OE	Output Enable Input
6	B ₁	B Side Input or 3-State Output
7	B ₀	B Side Input or 3-State Output
8	V _{CCB}	B Side Pow er Supply



Function Table

Control	Outputs
/OE	
L	Normal Operation
Н	3-State

H = HIGH Logic Level

L = LOW Logic Level

FXLA102 — Low-Voltage Dual-Supply 2-Bit Voltage Translator

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Conditions	Min.	Max.	Unit		
V _{CC}	Supply Voltage	VCCA	-0.5	4.6	V		
V CC	Supply Vollage	V _{CCB}	-0.5	4.6	v		
M.	DC Input Voltage	VO Ports A and B	-0.5	4.6	V		
Vı	DC Input Voltage	Control Input (/OE)	-0.5	4.6	v		
		Output 3-State	-0.5	4.6			
Vo	Output Voltage ⁽²⁾	Output Active (An)	-0.5	V _{CCA} +0.5	V		
		Output Active (B _n)	-0.5	V _{CCB} +0.5			
Ік	DC Input Diode Current	V _I <0V		-50	mA		
юк	DC Output Diada Current	V ₀ <0V		-50	mA		
ЮK	DC Output Diode Current	Vo>Vcc	-	+50	ШA		
юн/юг	DC Output Source/Sink Current		-50	+50	mA		
lcc	DC V _{CC} or Ground Current (per Supply	^r Pin)	-	±100	mA		
T _{STG}	Storage Temperature Range		-65	+150	°C		
PD	Pow er Dissipation		-	5	mW		
	Human Body Model, JESD22-A114	B Port I/O to GND		15			
ESD	Human Bouy Wouel, JESD22-A114	A Port I/O to GND		8	kV		
	Charged Device Model, JESD22-C101		2				

Notes:

1. Io absolute maximum ratings must be observed.

2. All unused inputs and input/outputs must be held at V_{CCi} or GND.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Conditions	Min.	Max.	Unit	
Vcc	Pow er Supply	Operating V _{CCA} or V _{CCB}	1.1	3.6	V	
Vin		Ports A and B	0	3.6	V	
VIN	Input Voltage	Control Input (/OE)	0	Vcca	V	
		$V_{CC} = 3.0 V \text{ to } 3.6 V$		±12		
		V_{CC} = 2.3 V to 2.7 V		±8		
	Dynamic Output Current IOH/IOL	$V_{CC} = 1.65 \text{ V}$ to 1.95 V		±5	mA	
		$V_{CC} = 1.40$ V to 1.65 V		±3		
		V _{CC} =1.1 V to 1.4 V		±2		
	Static Output Current	V _{CC} =1.1 V to 3.6 V		±4	μA	
TA	Operating Temperature, Free Air		-40	+85	°C	
dt/dV	Maximum Input Edge Rate	$V_{CCA/B} = 1.1$ to 3.6 V		10	ns/V	
Θја	Thermal Resistance			280	°C/W	

Power-Up/Power-Down Sequence

FXL translators offer an advantage in that either V_{CC} may be powered up first. This benefit derives from the chip design. When either V_{CC} is at 0 V, outputs are in a high-impedance state. The control input (/OE) is designed to track the V_{CCA} supply. A pull-up resistor tying /OE to V_{CCA} should be used to ensure that bus contention, excessive currents, or oscillations do not occur during power-up or power-dow n. The size of the pull-up resistor is based upon the current-sinking capability of the device driving the /OE pin.

The recommended power-up sequence is:

- 1. Apply pow er to the first V_{CC} .
- 2. Apply pow er to the second V_{CC} .
- 3. Drive the /OE input LOW to enable the device.

The recommended power-down sequence is:

- 1. Drive /OE input HIGH to disable the device.
- 2. Remove power from either V_{CC} .
- 3. Remove power from other $V_{\text{CC.}}$

Pull-Up/Pull-Down Resistors

<u>Do not use pull-up or pull-down resistors.</u> This device has bus-hold circuits: pull-up or pull-down resistors are not recommended because they interfere with the output state. The current through these resistors may exceed the hold drive, $I_{I(HOLD)}$ and/or $I_{I(OD)}$ bus-hold currents. The bus-hold feature eliminates the need for extra resistors.

DC Electrical Characteristics

T_A=-40 to 85°C.

Symbol	Parameter	Conditions	V _{CCA} (V)	V _{CCB} (V)	Min.	Тур.	Max.	Units
			2.70 to 3.60		2.00			
			2.30 to 2.70		1.60			
VIHA		Data Inputs A _n Control Pin /OE	1.65 to 2.30	1.10 to 3.60	.65xV _{CCA}			V
			1.40 to 1.65		.65xV _{CCA}			
	LEak Laural Issued Matterna		1.10 to 1.40		.90xV _{CCA}			
	High-Level Input Voltage			2.70 to 3.60	2.00			
				2.30 to 2.70	1.60			
V _{IHB}		Data Inputs B _n	1.10 to 3.60	1.65 to 2.30	.65xV _{CCB}			V
				1.40 to 1.65	.65хV _{CCB}			
				1.10 to 1.40	.90xV _{CCB}			
			2.70 to 3.60				.80	
			2.30 to 2.70				.70	
VILA		Data Inputs A _n Control Pin /OE	1.65 to 2.30	1.10 to 3.60			.35xV _{CCA}	V
			1.40 to 1.65				.35xV _{CCA}	
			1.10 to 1.40				.10xV _{CCA}	
	Low-Level Input Voltage			2.70 to 3.60			.80	V
				2.30 to 2.70			.70	
VILB		Data Inputs B _n	1.10 to 3.60	1.65 to 2.30			.35xV _{CCB}	
				1.40 to 1.65			.35xV _{CCB}	
				1.10 to 1.40			.10xV _{CCB}	
Voha	High-Level Output	I _{ОН} =-4 µА	1.10 to 3.60	1.10 to 3.60	V _{CCA} 40			
VOHB	Voltage ⁽³⁾	Іон=-4μ А	1.10 to 3.60	1.10 to 3.60	V _{ССВ} 40			V
Vola	Low - Leyel Output	l _{OL} =4 μA	1.10 to 3.60	1.10 to 3.60			.4	
Volb	Voltage ⁽³⁾	l _{OL} =4 μA	1.10 to 3.60	1.10 to 3.60			.4	V
		V _{IN} =0.80 V	3.00	3.00	75.0			
		V _{IN} =2.00 V	3.00	3.00	-75.0			
		V _{IN} =0.70 V	2.30	2.30	45.0			
		V _{IN} =1.60 V	2.30	2.30	-45.0			
	Bus-Hold Input Minimum	V _{IN} =0.57 V	1.65	1.65	25.0			
(HOLD)	Drive Current	V _{IN} =1.07 V	1.65	1.65	-25.0			μA
		V _{IN} =0.49 V	1.40	1.40	11.0			
		V _{IN} =0.91 V	1.40	1.40	-11.0			
		V _{IN} =0.11 V	1.10	1.10		4.0		-
		V _{IN} =0.99 V	1.10	1.10		-4.0		

Continued on following page...

DC Elec T _A =-40 to 8	ctrical Characteris	tics (Continued)					
Symbol	Parameter	Conditions	V _{CCA} (V)	V _{CCB} (V)	Min.	Max.	Units
			3.60	3.60	450.00		
	Bus-Hold Input		2.70	2.70	300.00		
I _(ODH)	Overdrive High	Data Inputs An, Bn	1.95	1.95	200.00		μA
	Current ⁽⁴⁾		1.60	1.60	120.00		
			1.40	1.40	80.00		
			3.60	3.60	-450.00		
	Bus-Hold Input		2.70	2.70	-300.00		
I _{I(ODL)}	Overdrive Low	Data Inputs An, Bn	1.95	1.95	-200.00		μA
	Current ⁽⁵⁾		1.60	1.60	-120.00		
			1.40	1.40	-80.00		
կ	Input Leakage Current	Control Inputs /OE, VI=V _{CCA} or GND	1.10 to 3.60	3.60		±1.0	μA
I	Pow er-Off Leakage	A _n Port V _O =0V to 3.6 V	0	3.6		±2.0	
OFF	Current	B_n Port V_O=0V to 3.6 V	3.60	0		±2.0	μA
		Data Outputs A _n , B _n V _O =0 V or 3.6 V, /OE=V _{IH}	3.60	3.60		±5.0	
loz	3-State Output Leakage	Data Outputs Data Outputs AnV _O =0 V or 3.6 V, /OE=GND	3.60	0		±5.0	μA
		Data Outputs B _n V _O =0 V or 3.6 V, /OE=GND	0	3.60		±5.0	
ICCA/B	Quiescent Supply Current ^(6, 7)	V _I =V _{CCI} or GND; I _O =0, /OE=GND	1.10 to 3.60	1.10 to 3.60		10.0	μA
lccz	Current ⁽ 6' 7 ⁾	$V_{I=}V_{CCI}$ or GND; $I_{O}=0$, /OE= V_{IH}	1.10 to 3.60	1.10 to 3.60		10.0	μA
ICCA		V _I =V _{CCB} or GND; I _O =0 B-to-A Direction,	0	1.10 to 3.60		-10.0	μA
IOCA	Quiescent Supply	/OE=GND	1.10 to 3.60	0		10.0	P'' '
Іссв	Current	V _I =V _{CCA} or GND; I ₀ =0, A-to-B Direction,	1.10 to 3.60	0		-10.0	μA
-000		/OE=GND	0	1.10 to 3.60		10.0	F

Notes:

3. This is the output voltage for static conditions. Dynamic drive specifications are given in the Dynamic Output Electrical Characteristics table.

4. An external drive must source at least the specified current to switch LOW-to-HIGH.

5. An external drive must source at least the specified current to switch HIGH-to-LOW.

6. V_{CCI} is the V_{CC} associated with the input side.

7. Reflects current per supply, V_{CCA} or V_{CCB}.

FXLA102 — Low-Voltage Dual-Supply 2-Bit Voltage Translator

Dynamic Output Electrical Characteristic

A Port (A_n)

Output Load: $C_L=15 \text{ pF}$, $R_L \ge M\Omega$ ($C_{VO}=4 \text{ pF}$), $T_A=-40 \text{ to } 85^{\circ}C$

Symbol	Parameter	V _{CCA} =3.0 V to 3.6 V		V _{CCA} =2.3 V to 2.7 V		V _{cca} =1.65 V to 1.95 V		V _{CCA} =1.4 V to 1.6 V		V _{CCA} =1.1 V to 1.3 V	Units
		Тур.	Max.	Тур.	Max.	Тур.	Max	Тур.	Max.	Тур.	
t _{rise}	Output Rise Time A Port ⁽ 9 ⁾		3.0		3.5		4.0		5.0	7.5	ns
t _{fall}	Output Fall Time A Port ⁽¹⁰⁾		3.0		3.5		4.0		5.0	7.5	ns
Юнд	Dynamic Output Current High ⁽ 9 ⁾	-11.4		-7.5		-4.7		-3.2		-1.7	mA
Юцр	Dynamic Output Current Low ⁽¹⁰⁾	+11.4		+7.5		+4.7		+3.2		+1.7	mA

B Port (B_n)

Output Load: $C_L=15 \text{ pF}$, $R_L \ge M\Omega$ ($C_{VO}=5 \text{ pF}$), $T_A=-40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V		V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		V _{CCB} =1.4 V to 1.6 V		V _{ссв} =1.1 V to 1.3 V	Units
-		Тур.	Max.	Тур.	Max.	Тур.	Max	Тур.	Max.	Тур.	
t _{rise}	Output Rise Time B Port ⁽ 9 ⁾		3.0		3.5		4.0		5.0	7.5	ns
t _{fall}	Output Fall Time B Port ⁽¹⁰⁾		3.0		3.5		4.0		5.0	7.5	ns
Юнд	Dynamic Output Current High ⁽ 9 ⁾	-12.0		-7.9		-5.0		-3.4		-1.8	mA
Юцр	Dynamic Output Current Low ⁽¹⁰⁾	+12.0		+7.9		+5.0		+3.4		+1.8	mA

Notes:

8. Dynamic output characteristics are guaranteed, but not tested.

9. See Figure 7.

10. See Figure 8.

AC Characteristics

$V_{CCA} = 3.0 V$ to 3.6 V, $T_A = -40$ to 85°C

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V		V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		V _{CCB} =1.4 V to 1.6 V		V _{CCB} =1.1 V to 1.3 V	Units
		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
tou tou	A to B	0.2	3.5	0.3	3.9	0.5	5.4	0.6	6.8	10.0	ns
t _{PLH} ,t _{PHL}	B to A	0.2	3.5	0.2	3.8	0.3	5.0	0.5	6.0	7.0	ns
t _{PZL} ,t _{PZH}	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹¹⁾		0.5		0.5		0.5		1.0	1.0	ns

V_{CCA} = 2.3 V to 2.7 V, T_A=-40 to 85°C

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V			V _{CCB} =2.3 V to 2.7 V		V _{CCB} =1.65 V to 1.95 V		⊧1.4 V .6 V	V _{CCB} =1.1 V to 1.3 V	Units
		Min.	Max.	Min.	Max.	Min.	Мах	Min.	Max.	Тур.	
++	A to B	0.2	3.8	0.4	4.2	0.5	5.6	0.8	6.9	10.5	ns
tplh,tphl	B to A	0.3	3.9	0.4	4.2	0.5	5.5	0.5	6.5	7.0	ns
t _{PZL} ,t _{PZH}	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹¹⁾		0.5		0.5		0.5		1.0	1.0	ns

$V_{CCA} = 1.65 \text{ V}$ to 1.95 V, $T_A = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{ссв} = to 3	=3.0 V 5.6 V	V _{ссв} = to 2	=2.3 V 2.7 V	V _{ссв} = to 1.	1.65 V 95 V	V _{ссв} = to 1	=1.4 V .6 V	V _{CCB} =1.1 V to 1.3 V	Units
-		Min.	Max.	Min.	Max.	Min.	Max	Min.	Max.	Тур.	
+ +	A to B	0.3	5.0	0.5	5.5	0.8	6.7	0.9	7.5	11.0	ns
t _{PLH} ,t _{PHL}	B to A	0.5	5.4	0.5	5.6	0.8	6.7	1.0	7.0	7.0	ns
tpzL,tpzH	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹¹⁾		0.5		0.5		0.5		1.0	1.0	ns

Note:

11. Skew is the variation of propagation delay between output signals and applies only to output signals on the same port (An or Bn) and switching with the same polarity (LOW-to-HIGH or HIGH-to-LOW) (see Figure 10). Skew is guaranteed, but not tested.

AC Characteristics (Continued)

$V_{CCA} = 1.4 V$ to 1.6 V, $T_{A} = -40$ to 85°C

- CCA	,	<i></i>									
Symbol	Parameter	V _{CCB} = to 3	=3.0 V 5.6 V		=2.3 V 2.7 V		1.65 V 95 V	V _{ссв} = to 1	=1.4 V .6 V	V _{CCB} =1.1 V to 1.3 V	Units
-		Min.	Max.	Min.	Max.	Min.	Мах	Min.	Max.	Тур.	
t _{PLH} ,t _{PHL}	A to B	0.5	6.0	0.5	6.5	1.0	7.0	1.0	8.5	11.5	ns
PLH, PHL	B to A	0.6	6.8	0.8	6.9	0.9	7.5	1.0	8.5	9.0	ns
tpzl,tpzh	/OE to A, /OE to B		1.7		1.7		1.7		1.7	1.7	μs
tskew	A Port, B Port ⁽¹²⁾		1.0		1.0		1.0		1.0	1.0	ns

$V_{CCA} = 1.1 \text{ V to } 1.3 \text{ V}, T_{A} = -40 \text{ to } 85^{\circ}\text{C}$

Symbol	Parameter	V _{CCB} =3.0 V to 3.6 V	V _{CCB} =2.3 V to 2.7 V	V _{CCB} =1.65 V to 1.95 V	V _{CCB} =1.4 V to 1.6 V	V _{CCB} =1.1 V to 1.3 V	Units
		Тур.	Тур.	Тур.	Тур.	Тур.	
tou tou	A to B	7.1	6.5	7.0	7.1	13.5	ns
t _{PLH} ,t _{PHL}	B to A	10.3	10.5	10.8	11.3	13.5	ns
,	/OE to A, /OE to B	1.7	1.7	1.7	1.7	1.7	μs
tskew	A Port, B Port ⁽¹²⁾	1.0	1.0	1.0	1.0	1.0	ns

Note:

Skew is the variation of propagation delay betw een output signals and applies only to output signals on the same port (A_n or B_n) and switching with the same polarity (LOW-to-HIGH or HIGH-to-LOW) (see Figure 10). Skew is guaranteed, but not tested.

Maximum Data Rate

T_A=-40 to 85°C.

V _{CCA}	V _{CCB} =3.0 V to 3.6 V	V _{CCB} =2.3 V to 2.7 V	V _{CCB} =1.65 V to 1.95 V	V _{CCB} =1.4 V to 1.6 V	V _{CCB} =1.1V to 1.3 V	Units
	Min.	Min.	Min.	Min.	Тур.	
$V_{CCA}=3.00$ V to 3.60 V	140	120	100	80	40	Mbps
$V_{\text{CCA}}\text{=}2.30$ V to 2.70 V	120	120	100	80	40	Mbps
$V_{CCA} \mbox{=} 1.65 \mbox{ V}$ to 1.95 $\mbox{ V}$	100	100	80	60	40	Mbps
$V_{CCA} = 1.40$ V to 1.60 V	80	80	60	60	40	Mbps
V _{CCA} =1.10 V to 1.30 V	Тур.	Тур.	Тур.	Тур.	Тур.	
VCCA=1.10 V 10 1.00 V	40	40	40	40	40	Mbps

Notes:

13. Maximum data rate is guaranteed, but not tested.

Maximum data rate is specified in megabits per second (see Figure 9). It is equivalent to two times the F-toggle frequency, specified in megahertz. For example, 100 Mbps is equivalent to 50 MHz.

Capacitance

Symbol	Parameter		Conditions	T _A =+25°C Typical	Units
CIN	Input Capacitance Control Pin (/OE)		V _{CCA} =V _{CCB} =GND	3	pF
CI/O Input / Output Capacitance		An	Vcca=Vccb=3.3V, /OE=Vcca	4	pF
U /0		Bn		5	۲'
C _{pd}	Pow er Dissipation Capacitance		$V_{CCA}=V_{CCB}=3.3 \text{ V}, V_I=0 \text{ V or } V_{CC}, f=10 \text{ MHz}$	25	pF

I/O Architecture Benefit

The FXLA102 I/O architecture benefits the end user, beyond level translation, in the following three ways:

Auto Direction without an external direction pin.

Drive Capacitive Loads. Automatically shifts to a higher current drive mode only during "Dynamic Mode" or HL / LH transitions.

Lower Power Consumption. Automatically shifts to low -power mode during "Static Mode" (no transitions), low ering pow er consumption.

The FXLA102 does not require a direction pin. Instead, the *V*O architecture detects input transitions on both side and automatically transfers the data to the corresponding output. For example, for a given channel, if both A and B side are at a static LOW, the direction has been established as $A \rightarrow B$, and a LH transition occurs on the B port; the FXLA102 internal *V*O architecture automatically changes direction from $A \rightarrow B$ to $B \rightarrow A$.

During HL / LH transitions, or "Dynamic Mode," a strong output driver drives the output channel in parallel with a weak output driver. After a typical delay of approximately 10 ns - 50 ns, the strong driver is turned off, leaving the weak driver enabled for holding the logic state of the channel. This weak driver is called the "bus

hold." "Static Mode" is when only the bus hold drives the channel. The bus hold can be over ridden in the event of a direction change. The strong driver allows the FXLA102 to quickly charge and discharge capacitive transmission lines during dynamic mode. Static mode conserves pow er, where I_{CC} is typically < 5 μ A.

Bus Hold Minimum Drive Current

Specifies the minimum amount of current the bus hold driver can source/sink. The bus hold minimum drive current (I_{HOLD}) is V_{CC} dependent and guaranteed in the DC Electrical tables. The intent is to maintain a valid output state in a static mode, but that can be overridden when an input data transition occurs.

Bus Hold Input Overdrive Drive Current

Specifies the minimum amount of current required (by an external device) to overdrive the bus hold in the event of a direction change. The bus hold overdrive (I_{ODH} , I_{ODL}) is V_{CC} dependent and guaranteed in the DC Electrical tables.

Dynamic Output Current

The strength of the output driver during LH / HL transitions is referenced on page 8, Dynamic Output Electrical Characteristics, I_{OHD}, and I_{OLD}.

Test Diagrams

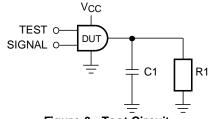


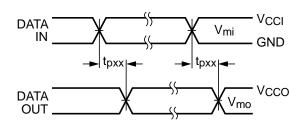
Figure 3. Test Circuit

Table 1. AC Test Conditions

Test	Input Signal	Output Enable Control
t _{PLH} , t _{PHL}	Data Pulses	0 V
t _{PZL}	0 V	HIGH to LOW Switch
tрzн	Vcci	HIGH to LOW Switch

Table 2. AC Load

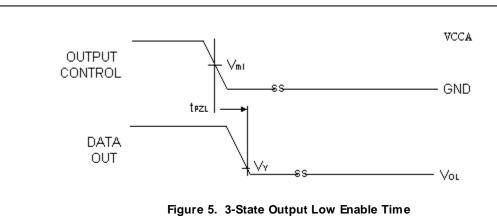
V _{cco}	C1	R1
1.2 V±0.1 V	15 pF	1 MΩ
1.5 V± 0.1 V	15 pF	1 MΩ
1.8 V ± 0.15 V	15 pF	1 MΩ
$2.5~\textrm{V}\pm0.2~\textrm{V}$	15 pF	1 MΩ
3.3 V ± 0.3 V	15 pF	1 MΩ





Notes:

- 15. Input $t_R = t_F = 2.0$ ns, 10% to 90%.
- 16. Input t_{R} = t_{F} = 2.5 ns, 10% to 90%, at V1= 3.0 V to 3.6 V only.



Notes:

17. Input $t_R = t_F = 2.0$ ns, 10% to 90%.

18. Input t_{R} = t_{F} = 2.5 ns, 10% to 90%, at V_I = 3.0 V to 3.6 V only.

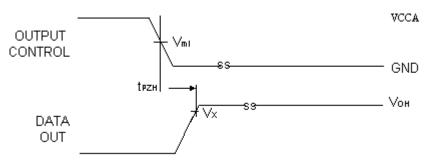


Figure 6. 3-State Output High Enable Time

Notes:

19. Input $t_{\scriptscriptstyle R}$ = $t_{\scriptscriptstyle F}$ = 2.0 ns, 10% to 90%.

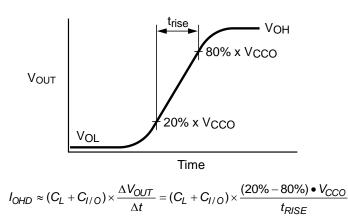
20. Input t_{R} = t_{F} = 2.5 ns, 10% to 90%, at V $_{\text{I}}$ = 3.0 V to 3.6 V only.

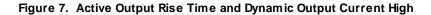
Table 3. Test Measure Points

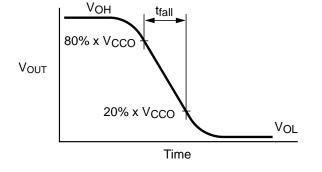
Symbol	V _{cc}
V _{MI} ⁽²¹⁾	V _{CCI} /2
V _{MO}	V _{CCo} /2
Vx	0.9 x V _{CCo}
V _Y	0.1 x V _{CCo}

Note:

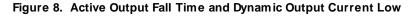
21. $V_{CCI}=V_{CCA}$ for control pin /OE or $V_{MI}=(V_{CCA}/2)$.

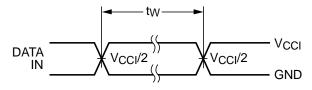






$$I_{OLD} \approx (C_L + C_{I/O}) \times \frac{\Delta V_{OUT}}{\Delta t} = (C_L + C_{I/O}) \times \frac{(80\% - 20\%) \bullet V_{CCO}}{t_{FALL}}$$





Maximum Data Rate, f = 1/t_W

Figure 9. Maximum Data Rate

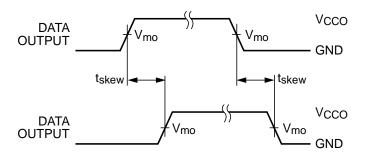


Figure 10. Output Skew Time

Note:

22. $t_{SKEW} = (t_{pHLmax} - t_{pHLmin}) \text{ or } (t_{pLHmax} - t_{pLHmin})$

